

## **KSP2907**

### **General Purpose Transistor**

- Collector-Emitter Voltage: V<sub>CEO</sub>= 40V
   Collector Dissipation: P<sub>C</sub>(max)=625mW



### 1. Emitter 2. Base 3. Collector

## **PNP Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-40	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-600	mA
P <sub>C</sub>	Collector Dissipation	625	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

## **Electrical Characteristics** $T_a=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -10\mu A, I_E = 0$	-60			V
BV <sub>CEO</sub>	* Collector Emitter Breakdown Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-40			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	-5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -50V, I <sub>E</sub> =0			-20	nA
h <sub>FE</sub>	DC Current Gain	$ \begin{split} & I_{C} \!\!= \!\! -0.1 \text{mA},  V_{CE} \!\!\!= \!\! -10 \text{V} \\ & V_{CE} \!\!\!= \!\!\! -10 \text{V},  I_{C} \!\!\!= \!\!\! -1 \text{mA} \\ & V_{CE} \!\!\!= \!\!\! -10 \text{V},  I_{C} \!\!\!= \!\!\! -10 \text{mA}, \\ & V_{CE} \!\!\!= \!\!\! -10 \text{V},  ^{1} I_{C} \!\!\!= \!\!\! -150 \text{mA} \\ & V_{CE} \!\!\!= \!\!\! -10 \text{V},  ^{1} I_{C} \!\!\!= \!\!\! -500 \text{mA} \end{split} $	35 50 75 100 30		300	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA			-0.4 -1.6	V V
V <sub>CE</sub> (sat)	Base Emitter Saturation Voltage	$I_C$ = -150mA, $I_B$ = -15mA $I_C$ = -500mA, $I_B$ = -50mA			-1.3 -2.6	V V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0 f=1MHz			8	pF
f <sub>T</sub>	* Current Gain Bandwidth Product	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -20V f=100MHz	200			MHz
t <sub>ON</sub>	Turn On Time	$V_{CC}$ = -30V, $I_{C}$ = -150mA $I_{B1}$ = -15mA			45	ns
t <sub>OFF</sub>	Turn Off Time	$V_{CC}$ = -6V, $I_{C}$ = -150mA $I_{B1}$ = $I_{B2}$ = -15mA			100	ns

<sup>\*</sup> Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%
\* Also available as a PN2907

# **Typical Characteristics**

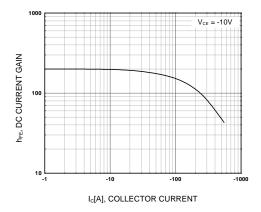


Figure 1. DC current Gain

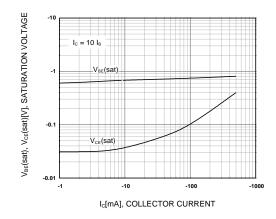


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

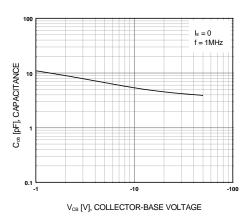


Figure 3. Output Capacitance

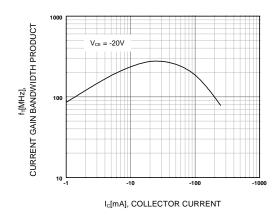
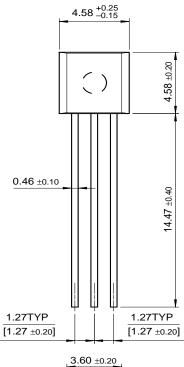
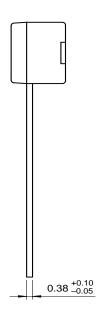


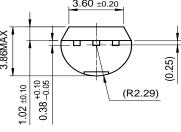
Figure 4. Current Gain Bandwidth Product

# **Package Demensions**

TO-92







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